

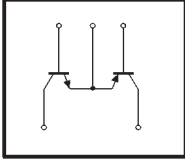
General purpose (dual transistors)

FMY5

●Features

- Both the 2SA1514K and 2SC3906K chips in an SMT package.
- PNP and NPN chips are connected in a common emitter configuration.

●Circuit diagram



●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-base voltage	V_{CB0}	120	V
Collector-emitter voltage	V_{CE0}	120	V
Emitter-base voltage	V_{EB0}	5	V
Collector current	I_C	50	mA
Power dissipation	P_C	300 (TOTAL)	mW *
Junction temperature	T_J	150	°C
Storage temperature	T_{stg}	-55~+150	°C

* 200mW per element must not be exceeded. PNP type negative symbols have been omitted.

●Package, marking, and packaging specifications

Part No.	FMY5
Package	SMT5
Marking	Y5
Code	T148
Basic ordering unit (pieces)	3000

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CB0}	120	—	—	V	$I_C=50/-50 \mu A$
Collector-emitter breakdown voltage	BV_{CE0}	120	—	—	V	$I_C=1/-1mA$
Emitter-base breakdown voltage	BV_{EB0}	5	—	—	V	$I_E=50/-50 \mu A$
Collector cutoff current	I_{CB0}	—	—	0.5	μA	$V_{CB}=100/-100V$
Emitter cutoff current	I_{EB0}	—	—	0.5	μA	$V_{EB}=4/-4V$
DC current transfer ratio	h_{FE}	120	—	820	—	$V_{CE}=6/-6V, I_C=2/-2mA$
Collector-emitter saturation voltage	$V_{CE(sat)}$	—	—	0.5	V	$I_C=10/-10mA, I_E=1/-0.1mA$
Transition frequency	f_T	—	140	—	MHz	$V_{CE}=12/-12V, I_E=2/-2mA, f=100MHz$ *
Output capacitance	C_{ob}	—	3/4	—	pF	$V_{CB}=12/-12V, I_E=0A, f=1MHz$

Note: The slash denotes NPN/PNP. PNP type negative symbols have been omitted. * Transition frequency of the device.

(94S-440-AC41)

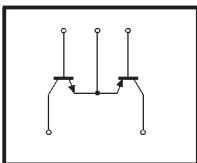
Totempoles (dual transistors)

FMY6

●Features

- Both the 2SA1036K and 2SC2411K chips in an SMT package.
- PNP and NPN chips are connected in a common emitter configuration.
- High $I_{Cmax.}$ (Max. 500mA)

●Circuit diagram



●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-base voltage	V_{CB0}	40	V
Collector-emitter voltage	V_{CE0}	32	V
Emitter-base voltage	V_{EB0}	5	V
Collector current	I_C	500	mA
Power dissipation	P_d	300 (TOTAL)	mW *
Junction temperature	T_J	150	°C
Storage temperature	T_{stg}	-55~+150	°C

* 200mW per element must not be exceeded. PNP type negative symbols have been omitted.

●Package, marking, and packaging specifications

Part No.	FMY6
Package	SMT5
Marking	Y6
Code	T148
Basic ordering unit (pieces)	3000

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CB0}	40	—	—	V	$I_C=100/-100 \mu A$
Collector-emitter breakdown voltage	BV_{CE0}	32	—	—	V	$I_C=1/-1mA$
Emitter-base breakdown voltage	BV_{EB0}	5	—	—	V	$I_E=100/-100 \mu A$
Collector cutoff current	I_{CB0}	—	—	1	μA	$V_{CB}=20/-20V$
Emitter cutoff current	I_{EB0}	—	—	1	μA	$V_{EB}=4/-4V$
Collector-emitter saturation voltage	$V_{CE(sat)}$	—	—	0.4	V	$I_C=100/-100mA, I_E=10/-10mA$
DC current transfer ratio	h_{FE}	120	—	—	—	$V_{CE}/I_C=3/-3V, I_C=10/-10mA$
Transition frequency	f_T	—	250/200	—	MHz	$V_{CE}=5/-5V, I_E=20/-20mA, f=200MHz$ *
Output capacitance	C_{ob}	—	6.5/7	—	pF	$V_{CE}=10/-10V, I_E=0A, f=1MHz$

Note: The slash denotes NPN/PNP. PNP type negative symbols have been omitted. * Transition frequency of mounted transistor.

(96-438-BD11)